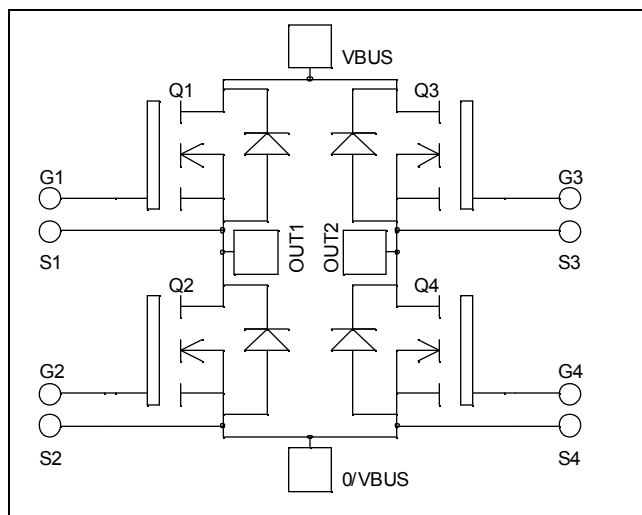


Full - Bridge MOSFET Power Module

$$V_{DSS} = 100V$$

$$R_{DSon} = 4.5m\Omega \text{ typ @ } T_j = 25^\circ C$$

$$I_D = 278A \text{ @ } T_c = 25^\circ C$$



Application

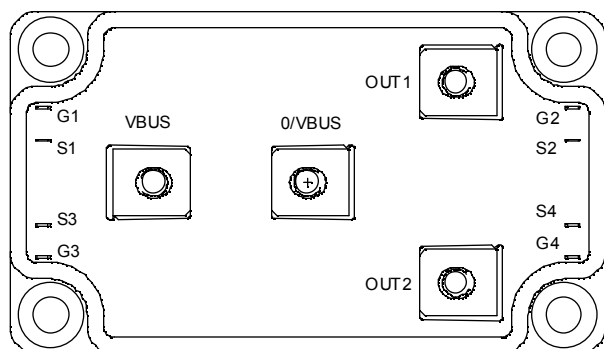
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS V[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	100	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	278
		$T_c = 80^\circ C$	207
I_{DM}	Pulsed Drain current	1100	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	5	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	780
I_{AR}	Avalanche current (repetitive and non repetitive)	100	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 100\text{V}$ $T_j = 25^\circ\text{C}$			200	μA
		$V_{GS} = 0\text{V}, V_{DS} = 80\text{V}$ $T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 125\text{A}$		4.5	5	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5\text{mA}$	2		4	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$			± 200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		20		nF
C_{oss}	Output Capacitance			8		
C_{rss}	Reverse Transfer Capacitance			2.9		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 50\text{V}$ $I_D = 250\text{A}$		700		nC
Q_{gs}	Gate – Source Charge			120		
Q_{gd}	Gate – Drain Charge			360		
$T_{d(on)}$	Turn-on Delay Time	Resistive Switching $V_{GS} = 15\text{V}$ $V_{Bus} = 66\text{V}$ $I_D = 250\text{A}$ $R_G = 2.5\Omega$		80		ns
T_r	Rise Time			165		
$T_{d(off)}$	Turn-off Delay Time			280		
T_f	Fall Time			135		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 25°C $V_{GS} = 15\text{V}, V_{Bus} = 66\text{V}$ $I_D = 250\text{A}, R_G = 2.5\Omega$		1.1		mJ
E_{off}	Turn-off Switching Energy ❷			1.2		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 125°C $V_{GS} = 15\text{V}, V_{Bus} = 66\text{V}$ $I_D = 250\text{A}, R_G = 2.5\Omega$		1.22		mJ
E_{off}	Turn-off Switching Energy ❷			1.28		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source current (Body diode)	$T_c = 25^\circ\text{C}$			278	A
		$T_c = 80^\circ\text{C}$			207	
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -250\text{A}$			1.3	V
dv/dt	Peak Diode Recovery ❸				5	V/ns
t_{rr}	Reverse Recovery Time	$I_S = -250\text{A}$ $V_R = 66\text{V}$ $di_S/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		190	ns
			$T_j = 125^\circ\text{C}$		370	
Q_{rr}	Reverse Recovery Charge	$I_S = -250\text{A}$ $V_R = 66\text{V}$ $di_S/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	0.8		μC
			$T_j = 125^\circ\text{C}$	3.4		

❶ E_{on} includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

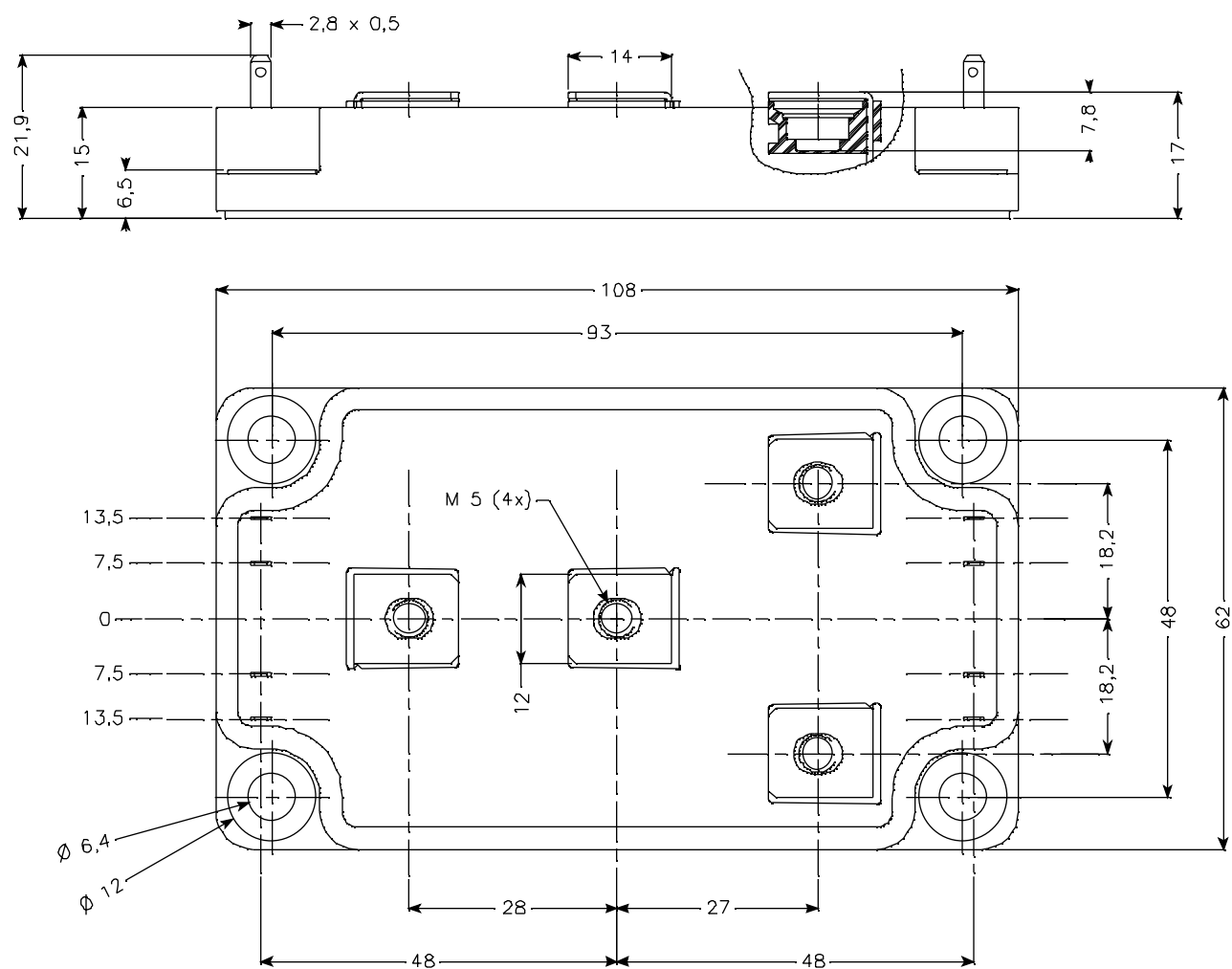
❸ dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$$I_S \leq -278\text{A} \quad di/dt \leq 200\text{A}/\mu\text{s} \quad V_R \leq V_{DSS} \quad T_j \leq 150^\circ\text{C}$$

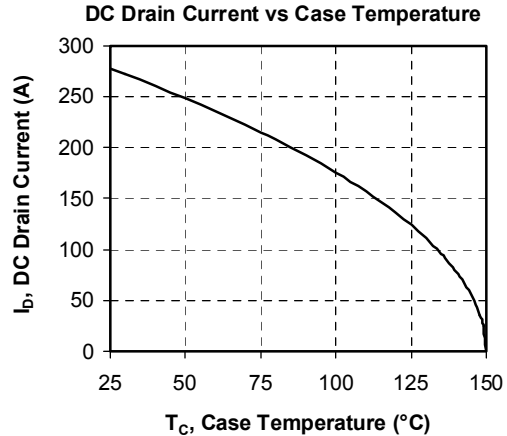
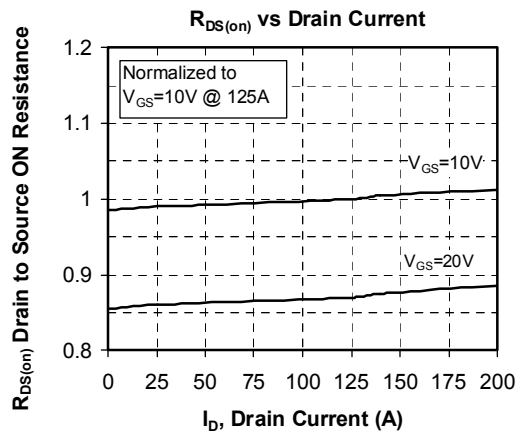
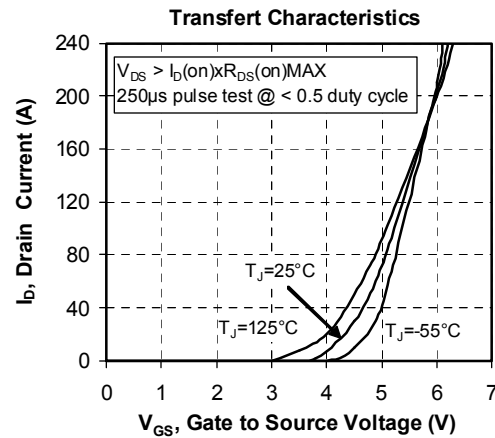
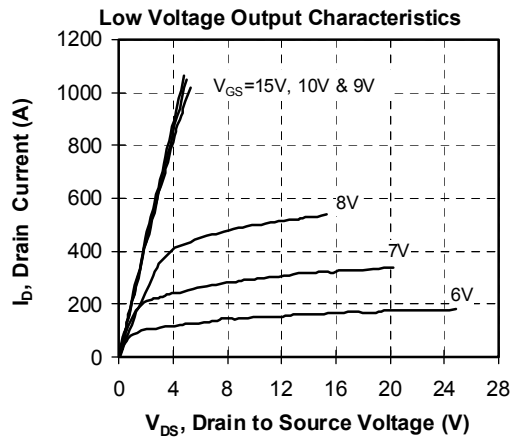
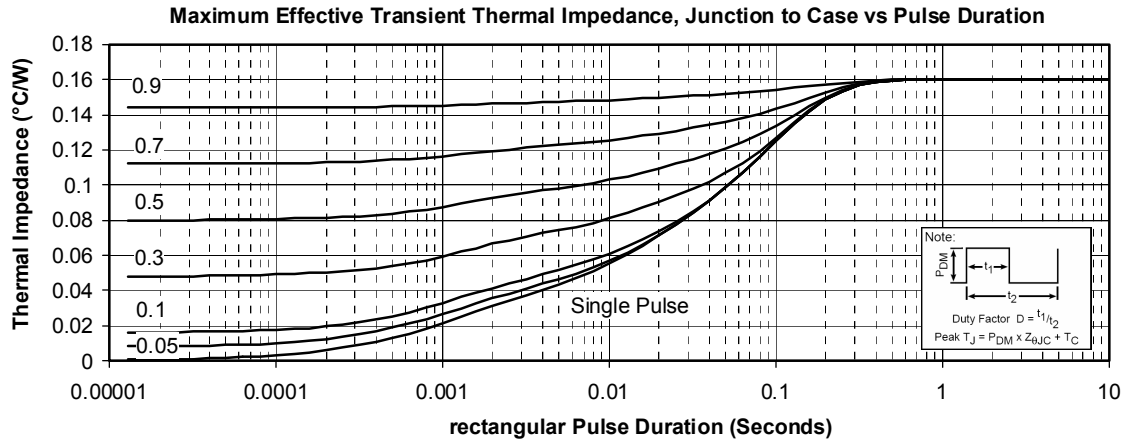
Thermal and package characteristics

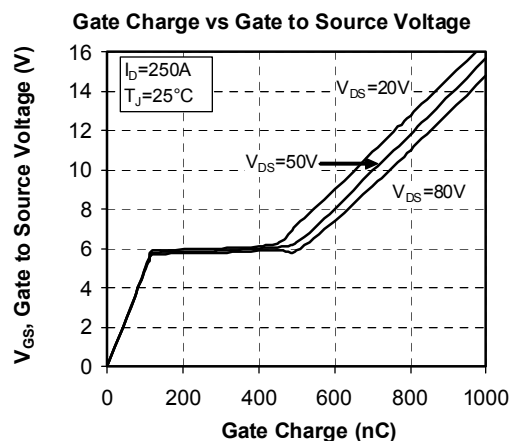
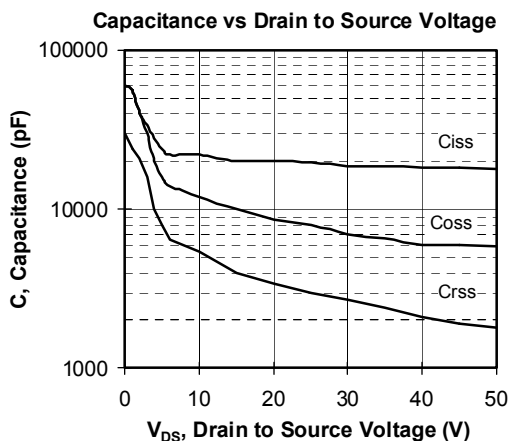
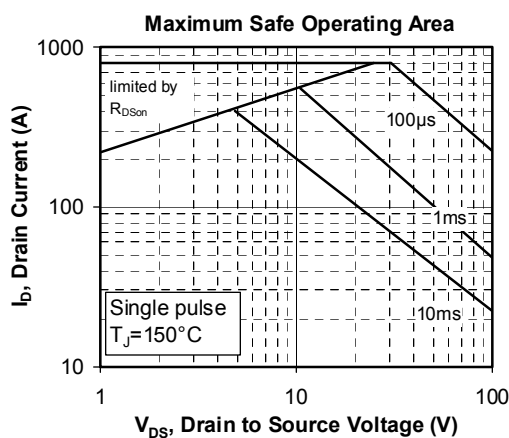
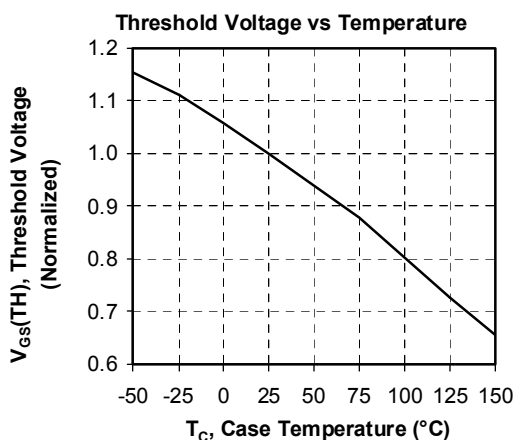
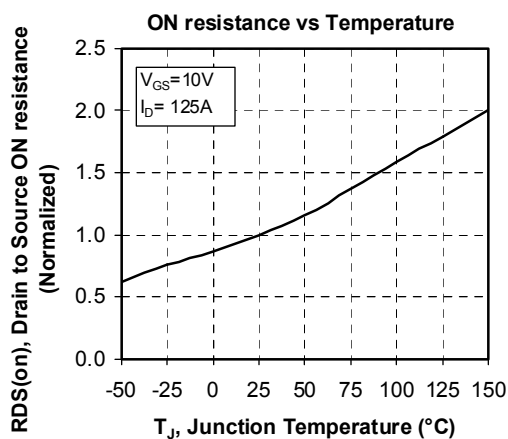
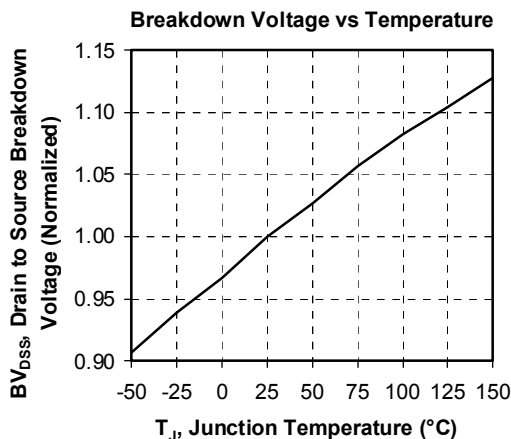
Symbol				Characteristic		Min	Typ	Max	Unit
R _{thJC}	Junction to Case							0.16	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz					2500			V
T _J	Operating junction temperature range					-40		150	°C
T _{STG}	Storage Temperature Range					-40		125	
T _C	Operating Case Temperature					-40		100	
Torque	Mounting torque	To heatsink		M6	3		5	N.m	
		For terminals		M5	2		3.5		
Wt	Package Weight							280	g

Package outline (dimensions in mm)

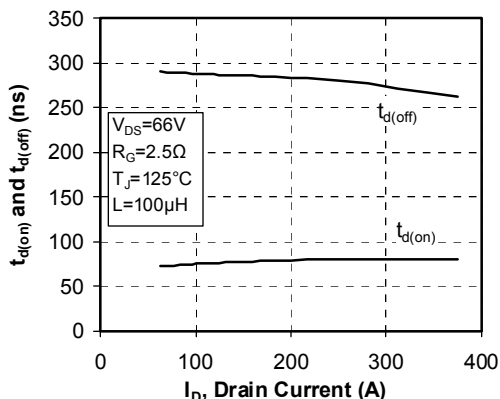


Typical Performance Curve

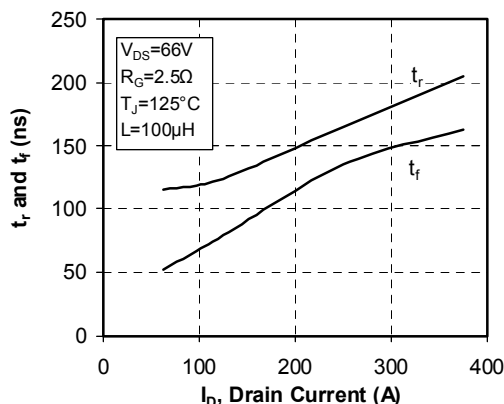




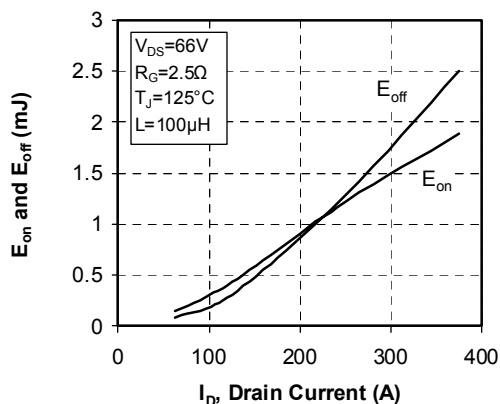
Delay Times vs Current



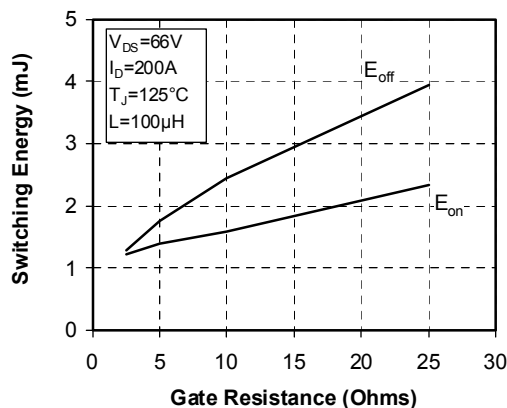
Rise and Fall times vs Current



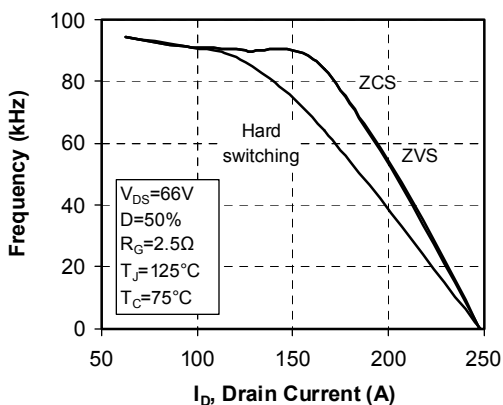
Switching Energy vs Current



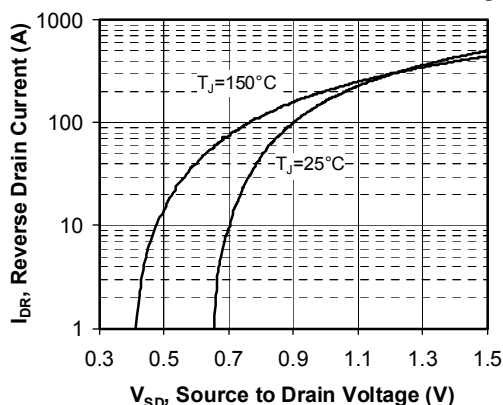
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.